

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM850-251CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 89.75 V/m; Power Drift = -0.07 dB

PMF = 2.830 is applied.

E-field emissions = 201.1 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

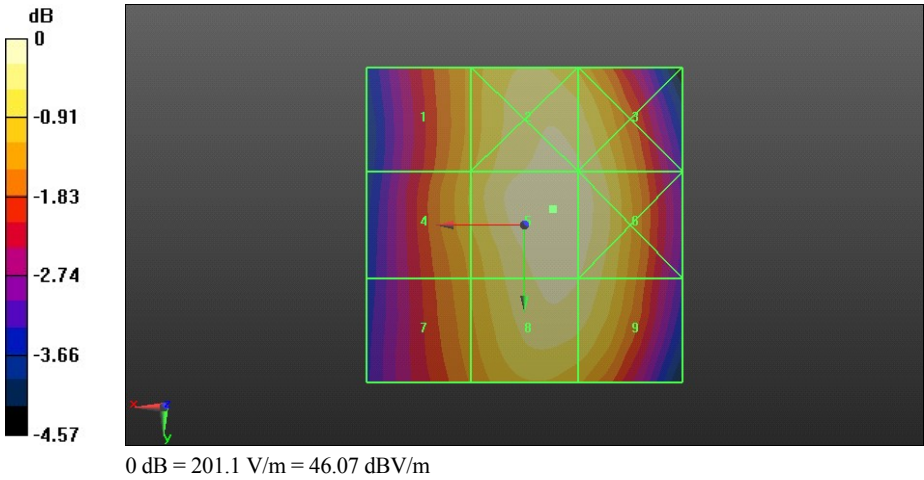
Grid 1 M3	Grid 2 M3	Grid 3 M3
179.8 V/m	198.0 V/m	195.8 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
182.1 V/m	201.1 V/m	198.6 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
175.9 V/m	196.3 V/m	194.3 V/m

Cursor:

Total = 201.1 V/m

E Category: M3

Location: -4.5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM850-190CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 91.84 V/m; Power Drift = -0.01 dB

PMF = 2.830 is applied.

E-field emissions = 205.7 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

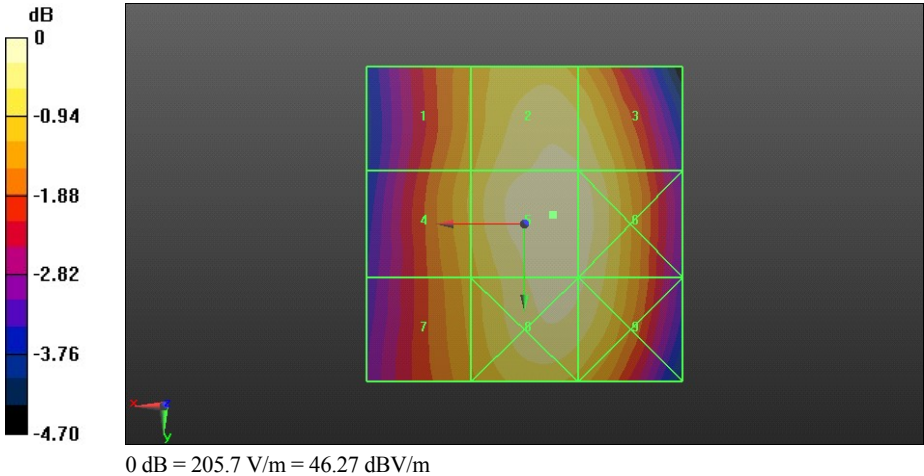
Grid 1 M3 183.3 V/m	Grid 2 M3 201.6 V/m	Grid 3 M3 199.4 V/m
Grid 4 M3 186.2 V/m	Grid 5 M3 205.7 V/m	Grid 6 M3 203.4 V/m
Grid 7 M3 181.8 V/m	Grid 8 M3 202.1 V/m	Grid 9 M3 200.0 V/m

Cursor:

Total = 205.7 V/m

E Category: M3

Location: -4.5, -1.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM850-128CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

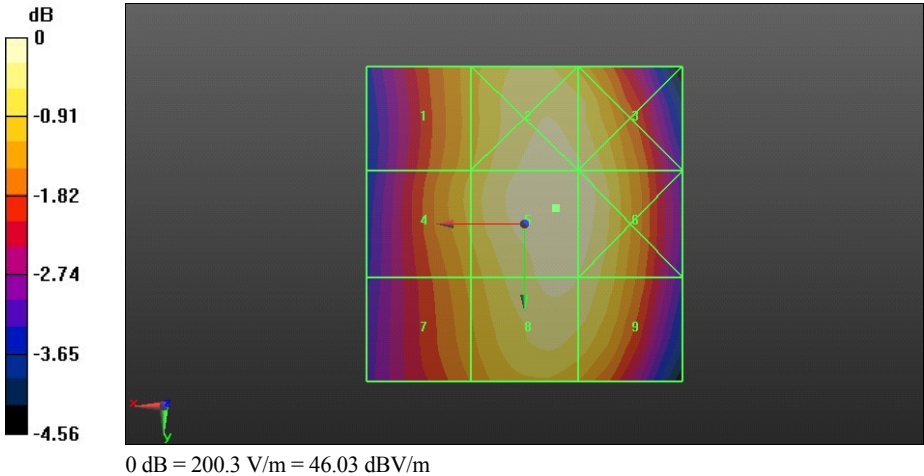
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 89.61 V/m; Power Drift = -0.06 dB
PMF = 2.830 is applied.
E-field emissions = 200.3 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 180.2 V/m	Grid 2 M3 197.6 V/m	Grid 3 M3 195.4 V/m
Grid 4 M3 183.1 V/m	Grid 5 M3 200.3 V/m	Grid 6 M3 198.9 V/m
Grid 7 M3 176.4 V/m	Grid 8 M3 195.5 V/m	Grid 9 M3 193.4 V/m

Cursor:
Total = 200.3 V/m
E Category: M3
Location: -5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM850-190CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 92.22 V/m; Power Drift = -0.05 dB

PMF = 2.830 is applied.

E-field emissions = 207.2 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

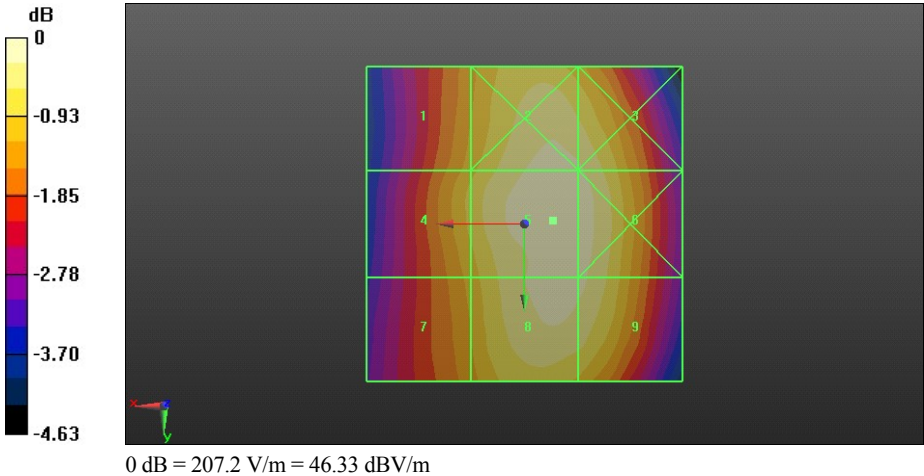
Grid 1 M3 183.9 V/m	Grid 2 M3 203.3 V/m	Grid 3 M3 201.3 V/m
Grid 4 M3 188.6 V/m	Grid 5 M3 207.2 V/m	Grid 6 M3 204.7 V/m
Grid 7 M3 182.7 V/m	Grid 8 M3 202.5 V/m	Grid 9 M3 201.8 V/m

Cursor:

Total = 207.2 V/m

E Category: M3

Location: -4.5, -0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM1900-810CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

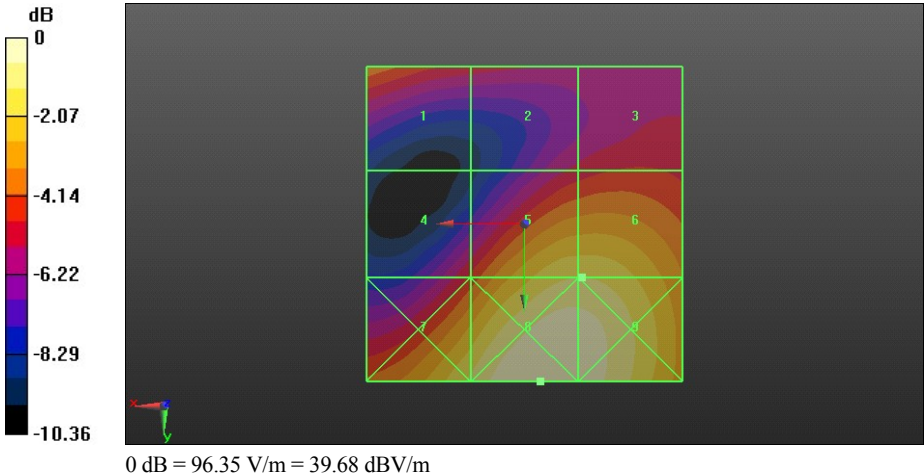
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 24.11 V/m; Power Drift = 0.01 dB
PMF = 2.860 is applied.
E-field emissions = 82.18 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
64.05 V/m	54.07 V/m	55.86 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
56.71 V/m	82.17 V/m	82.18 V/m
Grid 7 M3	Grid 8 M2	Grid 9 M2
83.89 V/m	96.35 V/m	94.38 V/m

Cursor:
Total = 96.35 V/m
E Category: M2
Location: -2.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM1900-661CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

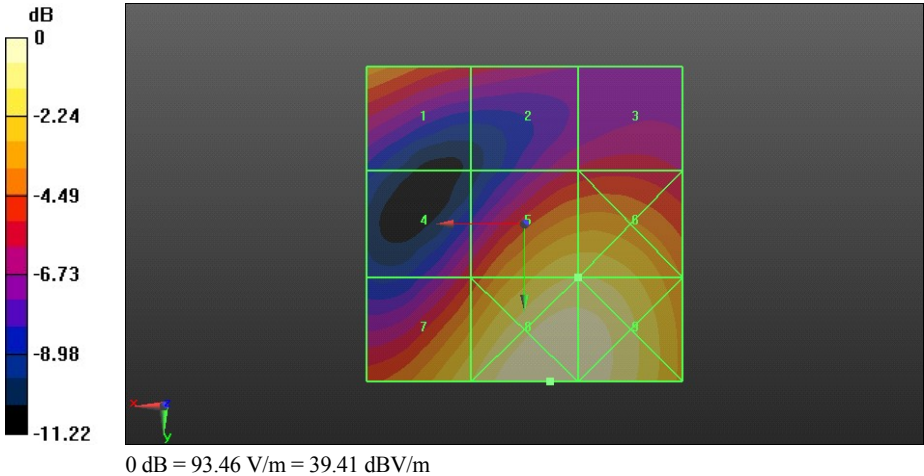
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 22.95 V/m; Power Drift = -0.01 dB
PMF = 2.860 is applied.
E-field emissions = 78.99 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
64.45 V/m	50.46 V/m	49.93 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
51.41 V/m	78.99 V/m	79.02 V/m
Grid 7 M3	Grid 8 M2	Grid 9 M2
78.58 V/m	93.46 V/m	91.86 V/m

Cursor:
Total = 93.46 V/m
E Category: M2
Location: -4, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM1900-512CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

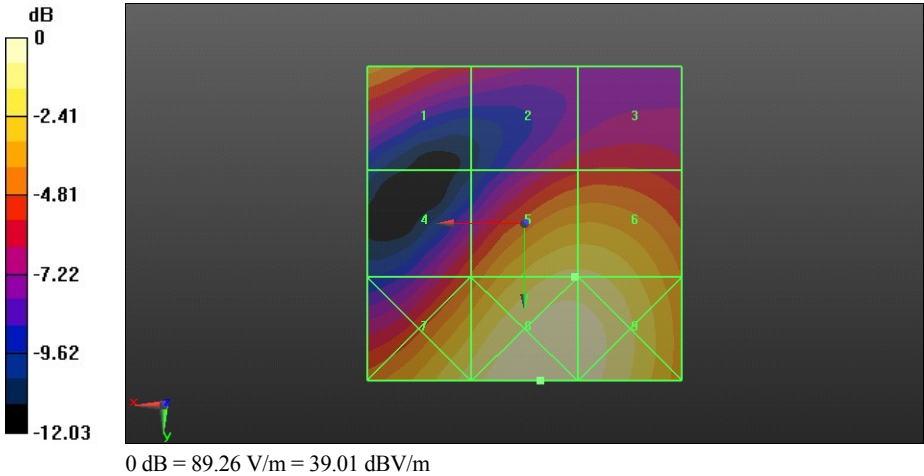
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 23.39 V/m; Power Drift = -0.09 dB
PMF = 2.860 is applied.
E-field emissions = 76.30 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 59.57 V/m	Grid 2 M4 46.09 V/m	Grid 3 M3 47.52 V/m
Grid 4 M3 52.28 V/m	Grid 5 M3 76.30 V/m	Grid 6 M3 76.27 V/m
Grid 7 M3 78.10 V/m	Grid 8 M2 89.26 V/m	Grid 9 M2 86.80 V/m

Cursor:
Total = 89.26 V/m
E Category: M2
Location: -2.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-GSM1900-810CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

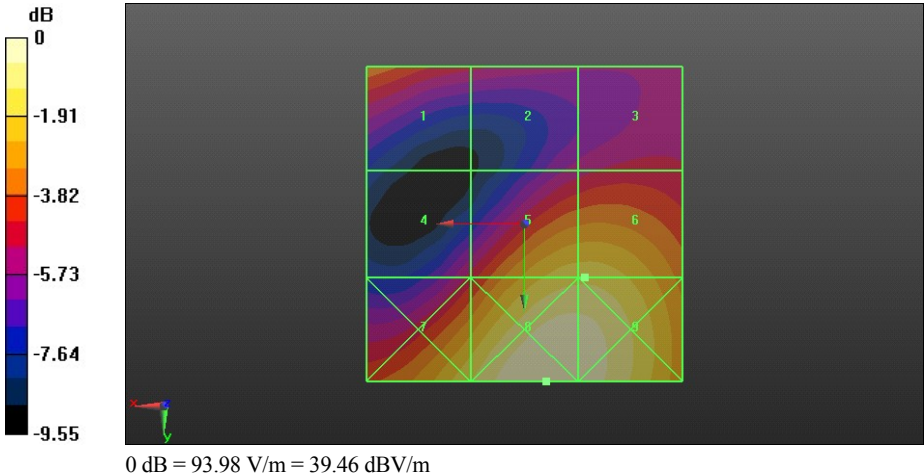
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 22.67 V/m; Power Drift = 0.05 dB
PMF = 2.860 is applied.
E-field emissions = 79.58 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 64.85 V/m	Grid 2 M3 53.97 V/m	Grid 3 M3 54.02 V/m
Grid 4 M3 54.22 V/m	Grid 5 M3 79.50 V/m	Grid 6 M3 79.58 V/m
Grid 7 M3 81.09 V/m	Grid 8 M2 93.98 V/m	Grid 9 M2 92.20 V/m

Cursor:
Total = 93.98 V/m
E Category: M2
Location: -3.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band II-9538CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

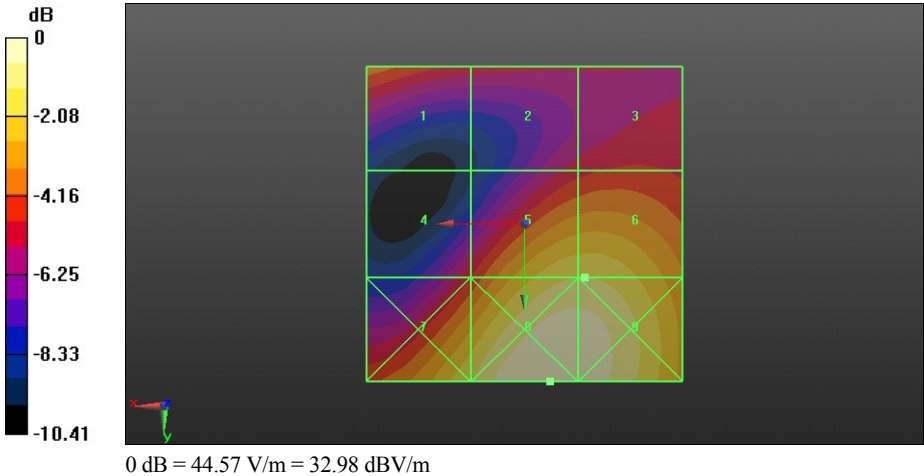
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 30.69 V/m; Power Drift = 0.05 dB
PMF = 1.020 is applied.
E-field emissions = 38.05 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
29.43 V/m	25.07 V/m	25.91 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
25.63 V/m	38.02 V/m	38.05 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
38.11 V/m	44.57 V/m	43.86 V/m

Cursor:
Total = 44.57 V/m
E Category: M4
Location: -4, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band II-9400CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

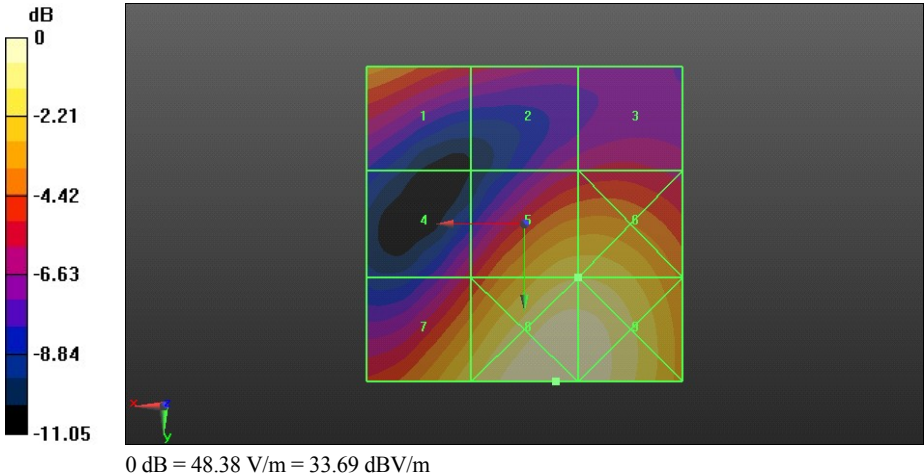
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 32.62 V/m; Power Drift = -0.04 dB
PMF = 1.020 is applied.
E-field emissions = 40.68 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 33.38 V/m	Grid 2 M4 26.02 V/m	Grid 3 M4 25.49 V/m
Grid 4 M4 26.03 V/m	Grid 5 M4 40.68 V/m	Grid 6 M4 40.70 V/m
Grid 7 M4 40.23 V/m	Grid 8 M4 48.38 V/m	Grid 9 M4 47.64 V/m

Cursor:
Total = 48.38 V/m
E Category: M4
Location: -5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band II-9262CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

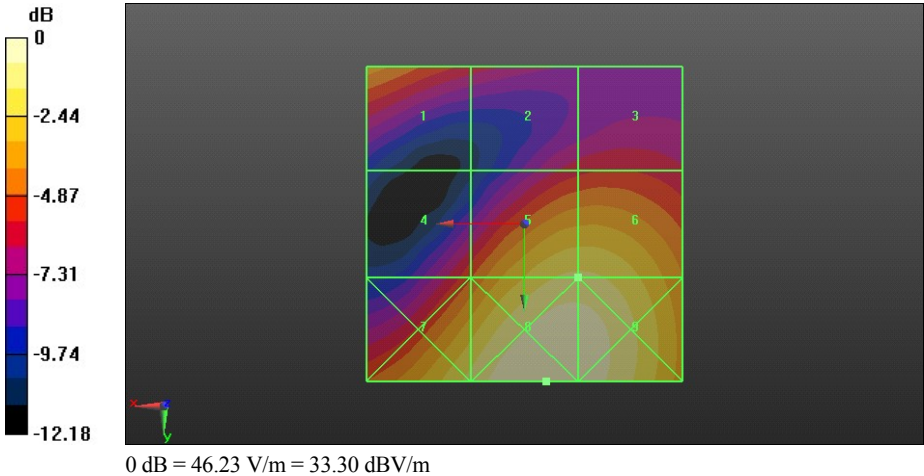
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 33.04 V/m; Power Drift = -0.10 dB
PMF = 1.020 is applied.
E-field emissions = 39.21 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
30.72 V/m	23.46 V/m	24.17 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
26.25 V/m	39.21 V/m	39.21 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
39.72 V/m	46.23 V/m	45.21 V/m

Cursor:
Total = 46.23 V/m
E Category: M4
Location: -3.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band II-9400CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

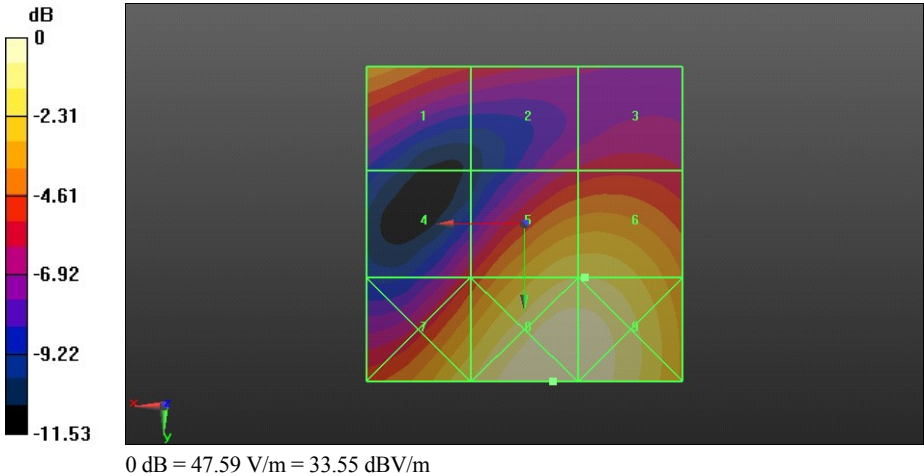
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 32.13 V/m; Power Drift = -0.09 dB
PMF = 1.020 is applied.
E-field emissions = 39.96 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
33.14 V/m	26.04 V/m	25.09 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
25.69 V/m	39.92 V/m	39.96 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
40.04 V/m	47.59 V/m	46.85 V/m

Cursor:
Total = 47.59 V/m
E Category: M4
Location: -4.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band IV-1513CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

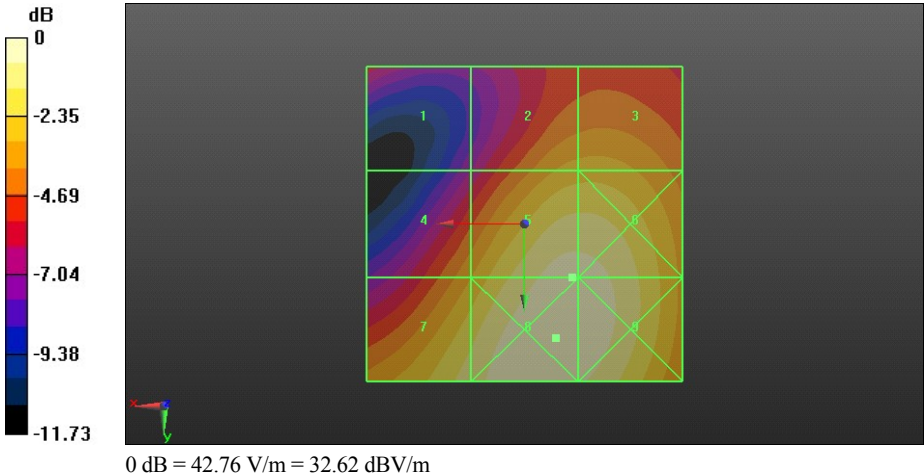
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 41.57 V/m; Power Drift = -0.04 dB
PMF = 1.020 is applied.
E-field emissions = 40.86 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
22.48 V/m	31.14 V/m	31.36 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
29.79 V/m	40.86 V/m	40.79 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
37.48 V/m	42.76 V/m	42.18 V/m

Cursor:
Total = 42.76 V/m
E Category: M4
Location: -5, 18, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band IV-1413CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

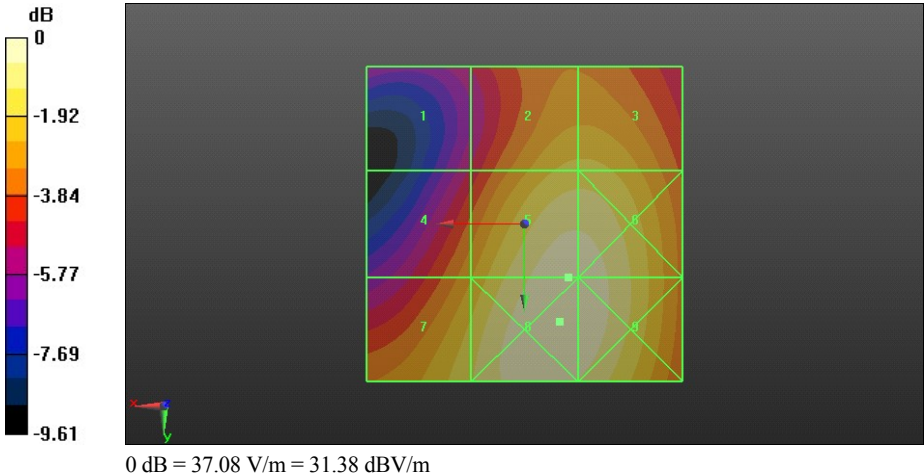
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 39.92 V/m; Power Drift = -0.03 dB
PMF = 1.020 is applied.
E-field emissions = 36.29 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
20.88 V/m	30.57 V/m	30.58 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
27.45 V/m	36.29 V/m	36.16 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
31.80 V/m	37.08 V/m	36.64 V/m

Cursor:
Total = 37.08 V/m
E Category: M4
Location: -5.5, 15.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band IV-1312CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

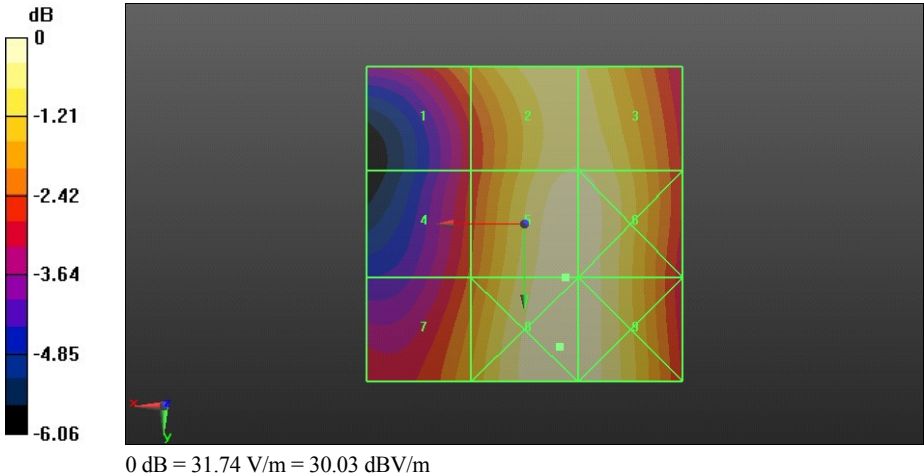
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 36.25 V/m; Power Drift = 0.07 dB
PMF = 1.020 is applied.
E-field emissions = 31.45 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
25.95 V/m	30.38 V/m	30.37 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
24.35 V/m	31.45 V/m	31.30 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
26.41 V/m	31.74 V/m	31.42 V/m

Cursor:
Total = 31.74 V/m
E Category: M4
Location: -5.5, 19.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band IV-1513CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

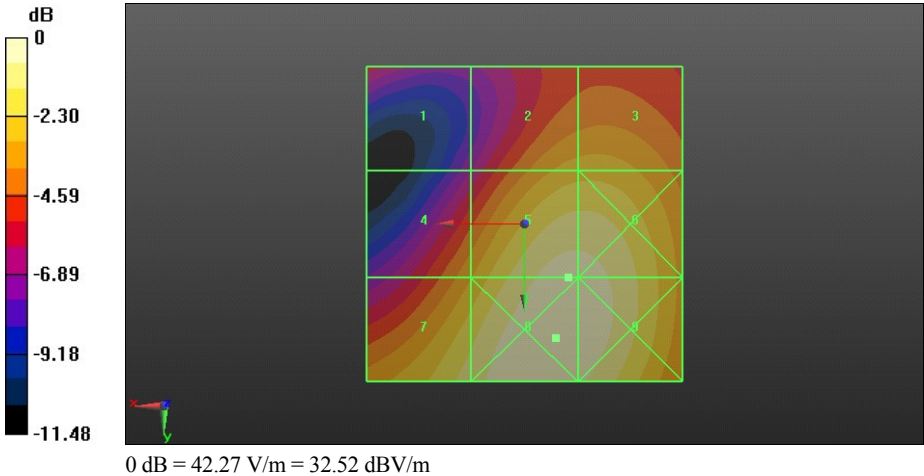
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 41.21 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 1.020 is applied.
E-field emissions = 40.50 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
22.56 V/m	31.16 V/m	31.38 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
29.55 V/m	40.50 V/m	40.42 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
37.06 V/m	42.27 V/m	41.69 V/m

Cursor:
Total = 42.27 V/m
E Category: M4
Location: -5, 18, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band V-4233CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

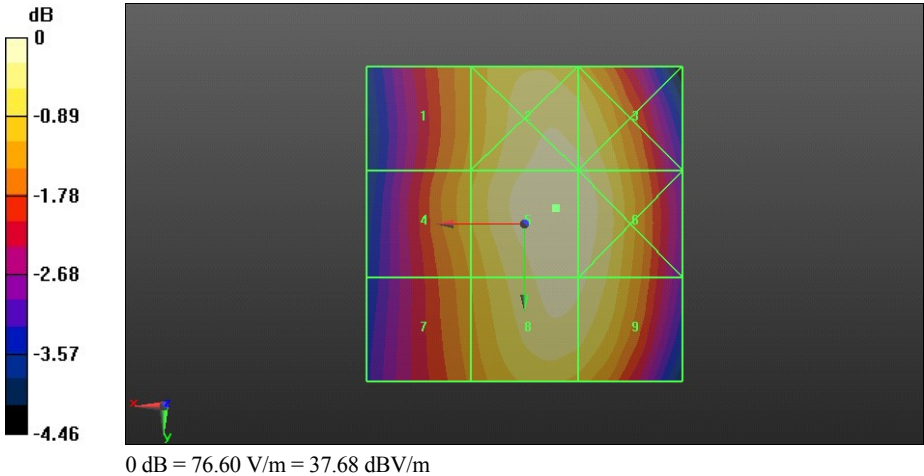
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 90.66 V/m; Power Drift = 0.07 dB
PMF = 1.040 is applied.
E-field emissions = 76.60 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
68.07 V/m	75.40 V/m	74.85 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
69.14 V/m	76.60 V/m	76.03 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
66.94 V/m	75.17 V/m	74.65 V/m

Cursor:
Total = 76.60 V/m
E Category: M4
Location: -5, -2.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band V-4182CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

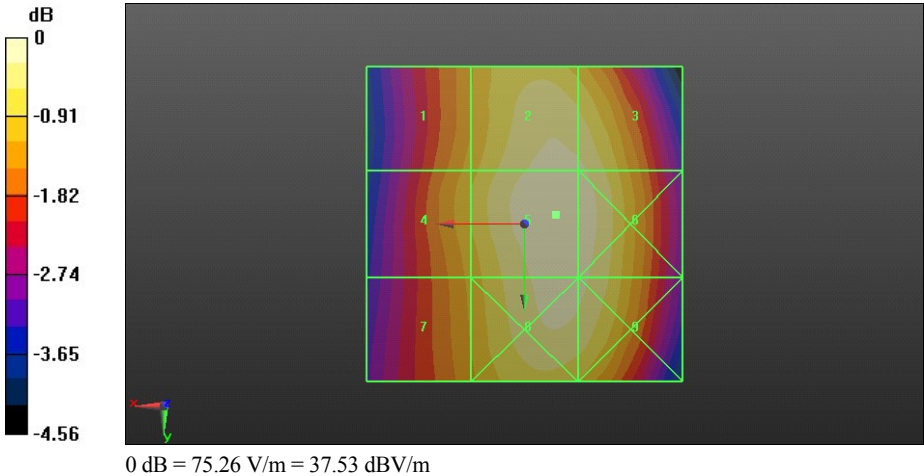
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 90.32 V/m; Power Drift = -0.05 dB
PMF = 1.040 is applied.
E-field emissions = 75.26 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
66.75 V/m	73.86 V/m	73.31 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
67.96 V/m	75.26 V/m	74.65 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
66.24 V/m	74.12 V/m	73.53 V/m

Cursor:
Total = 75.26 V/m
E Category: M4
Location: -5, -1.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band V-4132CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

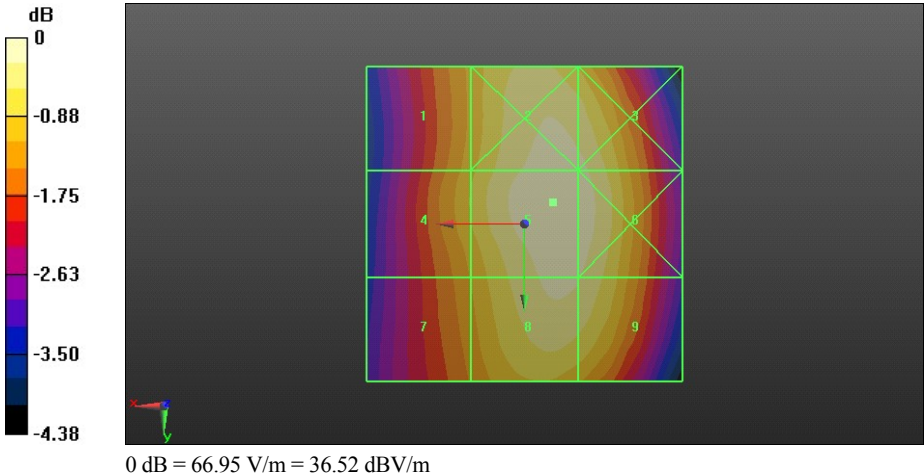
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 80.25 V/m; Power Drift = -0.04 dB
PMF = 1.040 is applied.
E-field emissions = 66.95 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
59.92 V/m	66.08 V/m	65.51 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
60.72 V/m	66.95 V/m	66.29 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
58.67 V/m	65.36 V/m	64.88 V/m

Cursor:
Total = 66.95 V/m
E Category: M4
Location: -4.5, -3.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_Y301-A2-UMTS Band V-4233CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

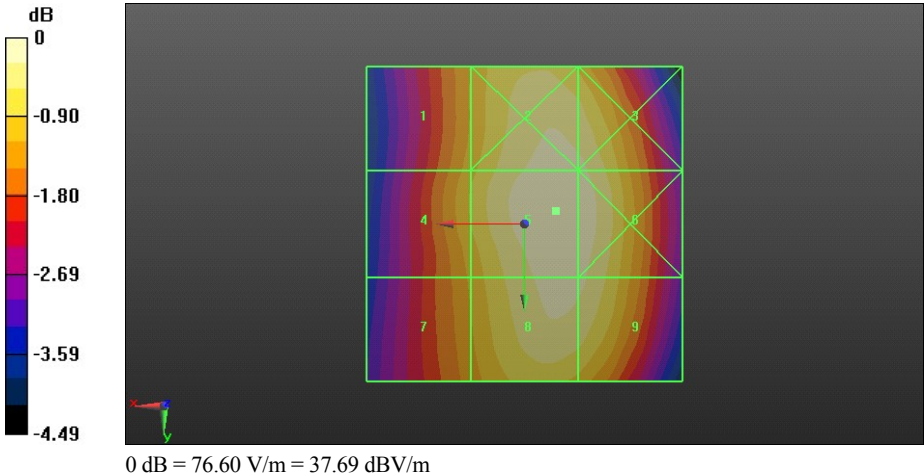
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 91.95 V/m; Power Drift = -0.10 dB
PMF = 1.040 is applied.
E-field emissions = 76.60 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
68.24 V/m	75.38 V/m	74.83 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
69.38 V/m	76.60 V/m	76.00 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
67.28 V/m	75.14 V/m	74.64 V/m

Cursor:
Total = 76.60 V/m
E Category: M4
Location: -5, -2, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM850-251CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09000 A/m; Power Drift = -0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.3287 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

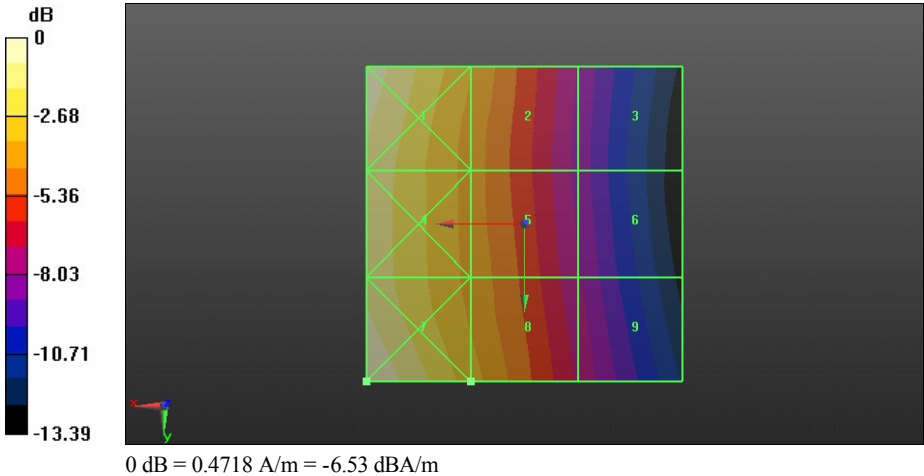
Grid 1 M3 0.457 A/m	Grid 2 M4 0.315 A/m	Grid 3 M4 0.186 A/m
Grid 4 M4 0.418 A/m	Grid 5 M4 0.303 A/m	Grid 6 M4 0.190 A/m
Grid 7 M3 0.472 A/m	Grid 8 M4 0.329 A/m	Grid 9 M4 0.204 A/m

Cursor:

Total = 0.4718 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM850-190CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08700 A/m; Power Drift = -0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.3175 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

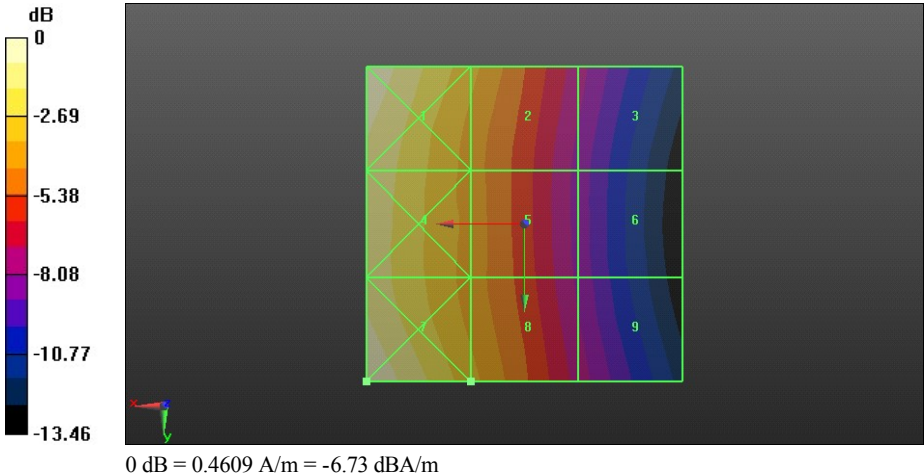
Grid 1 M3 0.455 A/m	Grid 2 M4 0.317 A/m	Grid 3 M4 0.191 A/m
Grid 4 M4 0.407 A/m	Grid 5 M4 0.293 A/m	Grid 6 M4 0.178 A/m
Grid 7 M3 0.461 A/m	Grid 8 M4 0.317 A/m	Grid 9 M4 0.194 A/m

Cursor:

Total = 0.4609 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM850-128CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08600 A/m; Power Drift = -0.06 dB

PMF = 2.820 is applied.

H-field emissions = 0.3173 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

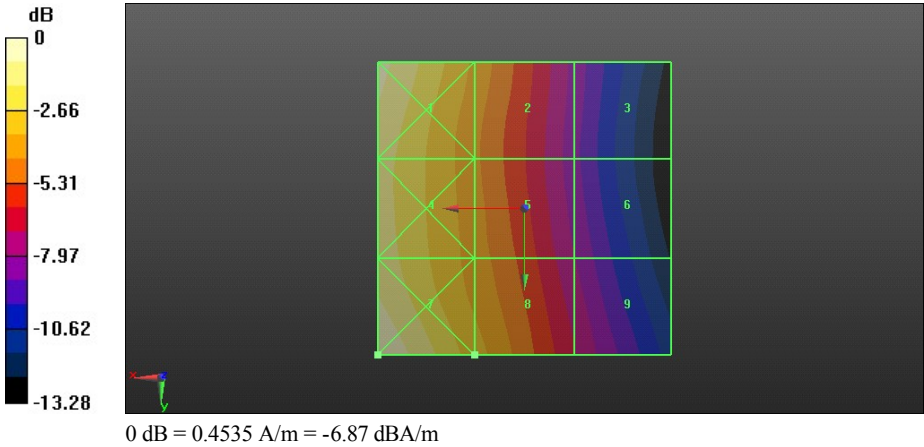
Grid 1 M4 0.427 A/m	Grid 2 M4 0.296 A/m	Grid 3 M4 0.175 A/m
Grid 4 M4 0.395 A/m	Grid 5 M4 0.288 A/m	Grid 6 M4 0.183 A/m
Grid 7 M3 0.454 A/m	Grid 8 M4 0.317 A/m	Grid 9 M4 0.203 A/m

Cursor:

Total = 0.4535 A/m

H Category: M3

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM850-251CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08900 A/m; Power Drift = 0.08 dB

PMF = 2.820 is applied.

H-field emissions = 0.3127 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

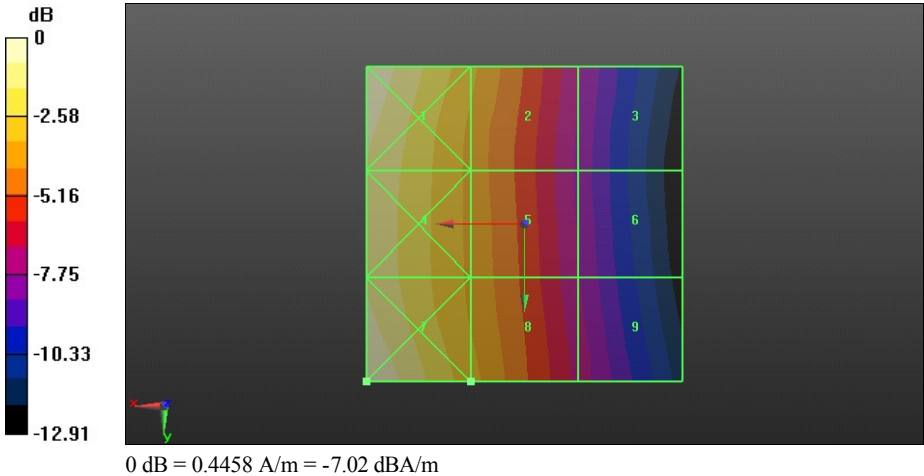
Grid 1 M4 0.439 A/m	Grid 2 M4 0.309 A/m	Grid 3 M4 0.186 A/m
Grid 4 M4 0.402 A/m	Grid 5 M4 0.294 A/m	Grid 6 M4 0.185 A/m
Grid 7 M4 0.446 A/m	Grid 8 M4 0.313 A/m	Grid 9 M4 0.196 A/m

Cursor:

Total = 0.4458 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM1900-810CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

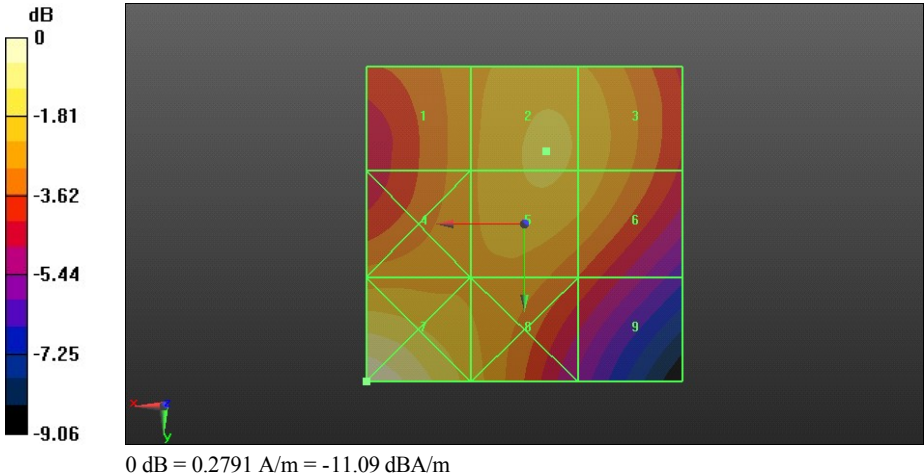
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08900 A/m; Power Drift = 0.01 dB
PMF = 2.830 is applied.
H-field emissions = 0.2297 A/m
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M3 0.208 A/m	Grid 2 M3 0.230 A/m	Grid 3 M3 0.225 A/m
Grid 4 M3 0.209 A/m	Grid 5 M3 0.229 A/m	Grid 6 M3 0.223 A/m
Grid 7 M2 0.279 A/m	Grid 8 M3 0.220 A/m	Grid 9 M3 0.184 A/m

Cursor:
Total = 0.2791 A/m
H Category: M2
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM1900-661CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08300 A/m; Power Drift = 0.04 dB

PMF = 2.830 is applied.

H-field emissions = 0.2107 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

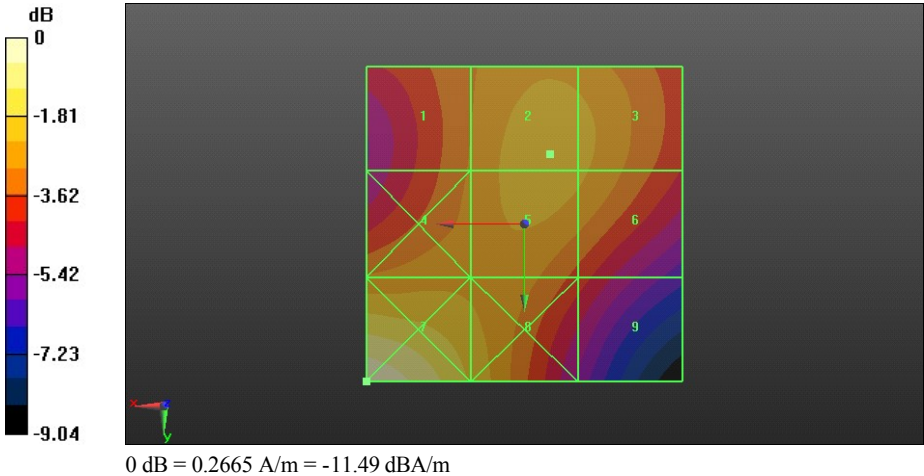
Grid 1 M3 0.190 A/m	Grid 2 M3 0.211 A/m	Grid 3 M3 0.207 A/m
Grid 4 M3 0.199 A/m	Grid 5 M3 0.210 A/m	Grid 6 M3 0.205 A/m
Grid 7 M2 0.266 A/m	Grid 8 M3 0.215 A/m	Grid 9 M3 0.171 A/m

Cursor:

Total = 0.2665 A/m

H Category: M2

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM1900-512CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

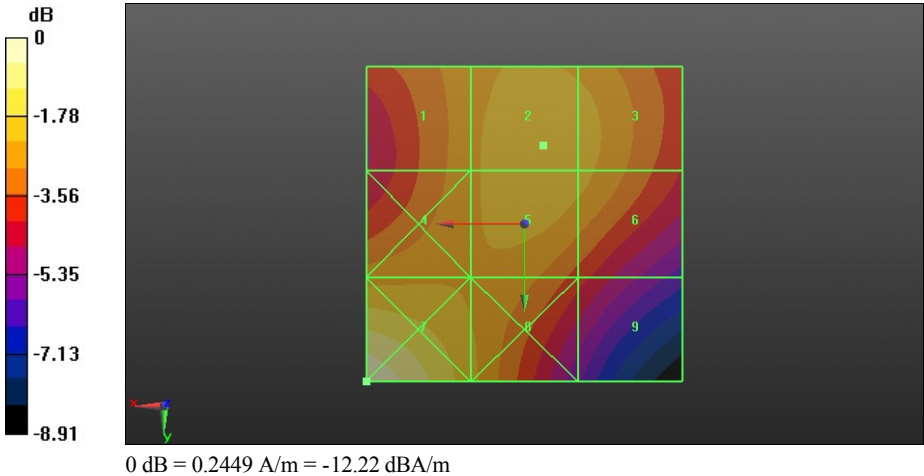
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07900 A/m; Power Drift = -0.01 dB
PMF = 2.830 is applied.
H-field emissions = 0.1982 A/m
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M3 0.183 A/m	Grid 2 M3 0.198 A/m	Grid 3 M3 0.193 A/m
Grid 4 M3 0.185 A/m	Grid 5 M3 0.197 A/m	Grid 6 M3 0.191 A/m
Grid 7 M3 0.245 A/m	Grid 8 M3 0.191 A/m	Grid 9 M3 0.157 A/m

Cursor:
Total = 0.2449 A/m
H Category: M3
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-GSM1900-810CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

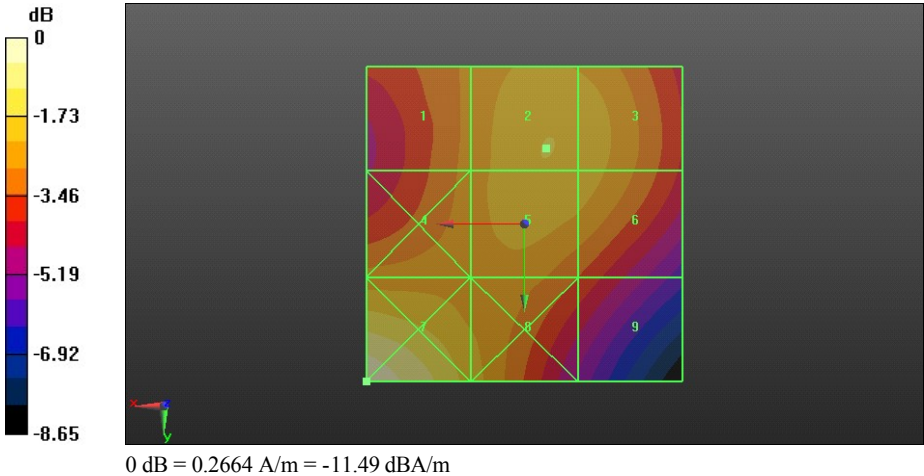
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08400 A/m; Power Drift = 0.10 dB
PMF = 2.830 is applied.
H-field emissions = 0.2187 A/m
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 M3 0.197 A/m	Grid 2 M3 0.219 A/m	Grid 3 M3 0.215 A/m
Grid 4 M3 0.200 A/m	Grid 5 M3 0.218 A/m	Grid 6 M3 0.213 A/m
Grid 7 M2 0.266 A/m	Grid 8 M3 0.212 A/m	Grid 9 M3 0.179 A/m

Cursor:
Total = 0.2664 A/m
H Category: M2
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band II-9538CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

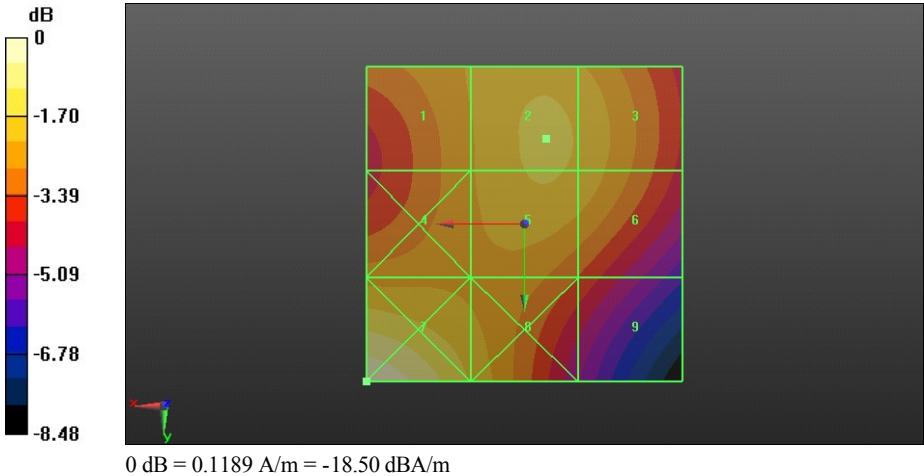
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1050 A/m; Power Drift = -0.03 dB
PMF = 1.010 is applied.
H-field emissions = 0.09928 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.092 A/m	Grid 2 M4 0.099 A/m	Grid 3 M4 0.097 A/m
Grid 4 M4 0.091 A/m	Grid 5 M4 0.099 A/m	Grid 6 M4 0.096 A/m
Grid 7 M4 0.119 A/m	Grid 8 M4 0.097 A/m	Grid 9 M4 0.080 A/m

Cursor:
Total = 0.1189 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band II-9400CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

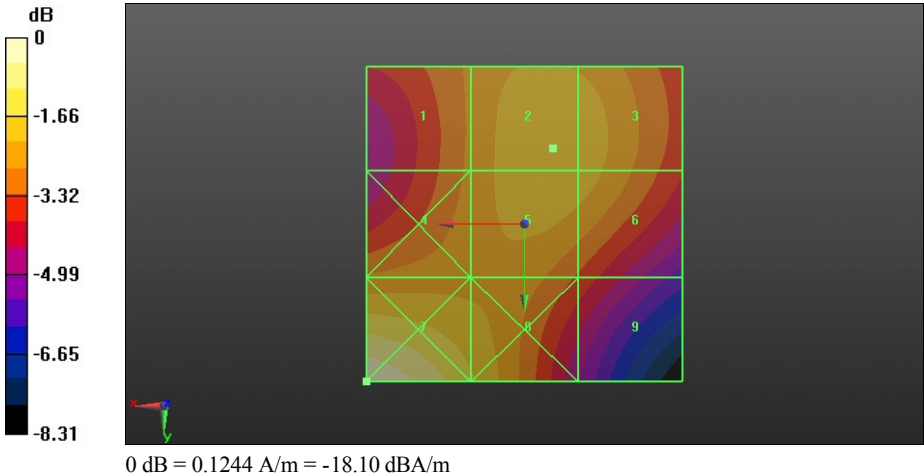
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1100 A/m; Power Drift = -0.03 dB
PMF = 1.010 is applied.
H-field emissions = 0.1022 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.092 A/m	Grid 2 M4 0.102 A/m	Grid 3 M4 0.101 A/m
Grid 4 M4 0.095 A/m	Grid 5 M4 0.102 A/m	Grid 6 M4 0.100 A/m
Grid 7 M4 0.124 A/m	Grid 8 M4 0.104 A/m	Grid 9 M4 0.084 A/m

Cursor:
Total = 0.1244 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band II-9262CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

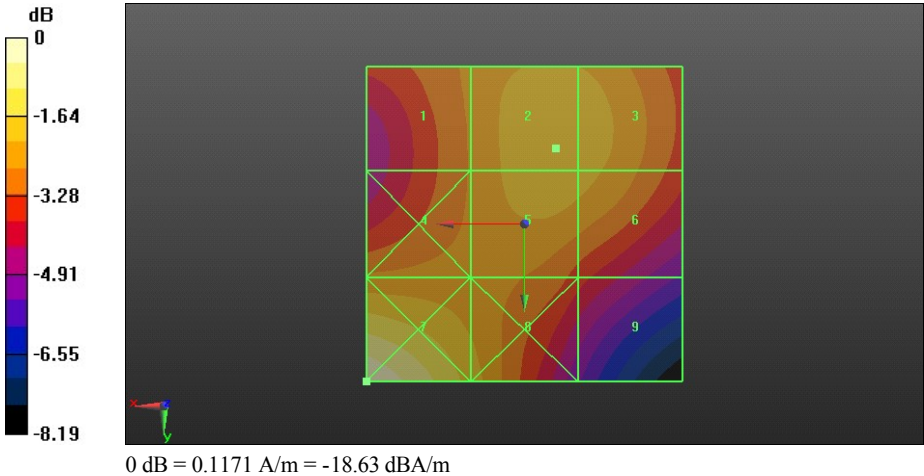
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1030 A/m; Power Drift = 0.06 dB
PMF = 1.010 is applied.
H-field emissions = 0.09582 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.087 A/m	Grid 2 M4 0.096 A/m	Grid 3 M4 0.095 A/m
Grid 4 M4 0.088 A/m	Grid 5 M4 0.095 A/m	Grid 6 M4 0.094 A/m
Grid 7 M4 0.117 A/m	Grid 8 M4 0.094 A/m	Grid 9 M4 0.078 A/m

Cursor:
Total = 0.1171 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band II-9400CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

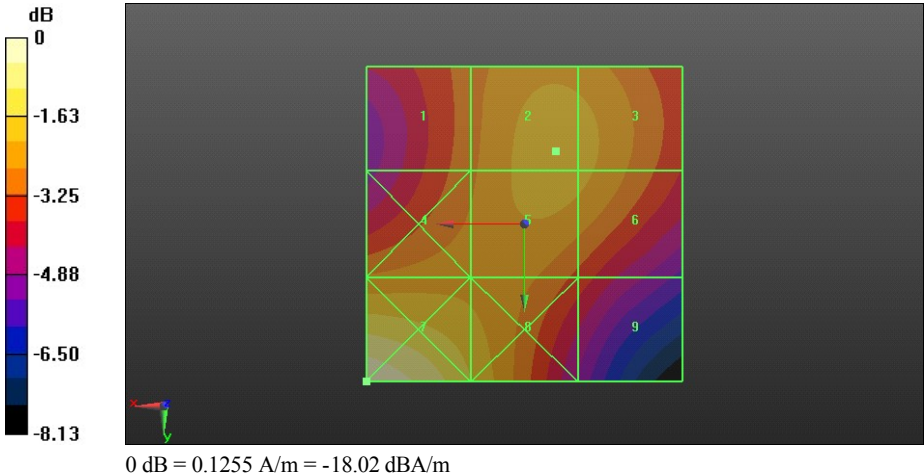
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1090 A/m; Power Drift = 0.12 dB
PMF = 1.010 is applied.
H-field emissions = 0.1014 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.091 A/m	Grid 2 M4 0.101 A/m	Grid 3 M4 0.100 A/m
Grid 4 M4 0.096 A/m	Grid 5 M4 0.101 A/m	Grid 6 M4 0.100 A/m
Grid 7 M4 0.126 A/m	Grid 8 M4 0.105 A/m	Grid 9 M4 0.085 A/m

Cursor:
Total = 0.1255 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band IV-1513CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

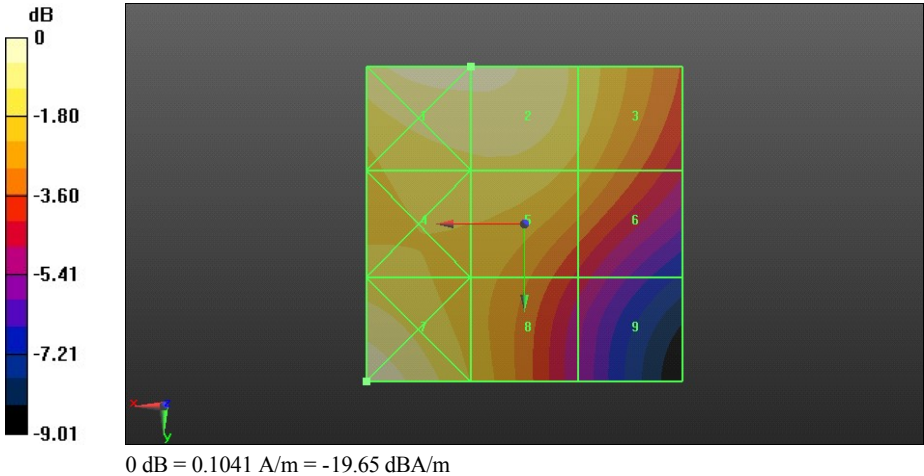
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09100 A/m; Power Drift = 0.05 dB
PMF = 0.9800 is applied.
H-field emissions = 0.09934 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.100 A/m	Grid 2 M4 0.099 A/m	Grid 3 M4 0.089 A/m
Grid 4 M4 0.089 A/m	Grid 5 M4 0.089 A/m	Grid 6 M4 0.082 A/m
Grid 7 M4 0.104 A/m	Grid 8 M4 0.085 A/m	Grid 9 M4 0.063 A/m

Cursor:
Total = 0.1041 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band IV-1413CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

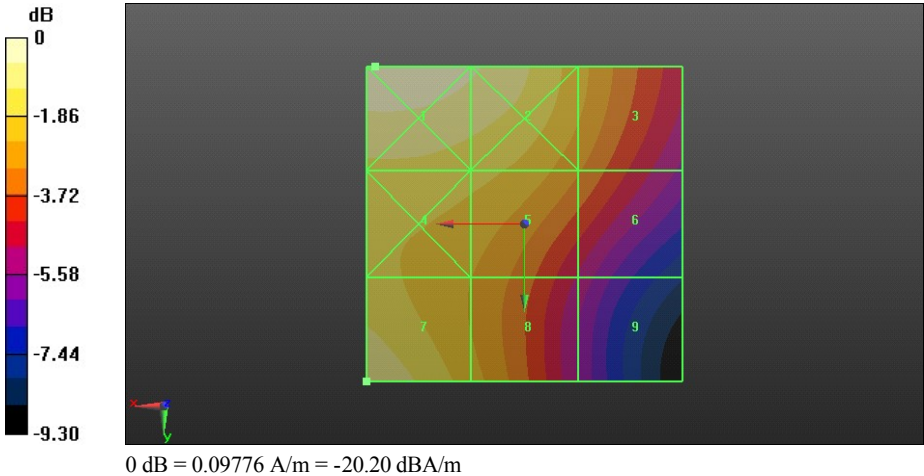
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07900 A/m; Power Drift = 0.04 dB
PMF = 0.9800 is applied.
H-field emissions = 0.09207 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.098 A/m	Grid 2 M4 0.092 A/m	Grid 3 M4 0.076 A/m
Grid 4 M4 0.084 A/m	Grid 5 M4 0.081 A/m	Grid 6 M4 0.069 A/m
Grid 7 M4 0.092 A/m	Grid 8 M4 0.076 A/m	Grid 9 M4 0.055 A/m

Cursor:
Total = 0.09776 A/m
H Category: M4
Location: 23.5, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band IV-1312CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

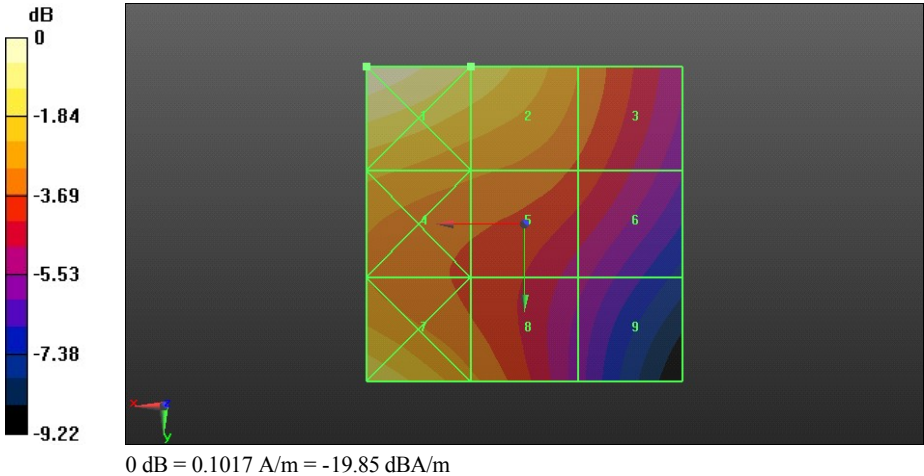
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07500 A/m; Power Drift = -0.07 dB
PMF = 0.9800 is applied.
H-field emissions = 0.08809 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.102 A/m	Grid 2 M4 0.088 A/m	Grid 3 M4 0.072 A/m
Grid 4 M4 0.079 A/m	Grid 5 M4 0.073 A/m	Grid 6 M4 0.066 A/m
Grid 7 M4 0.089 A/m	Grid 8 M4 0.073 A/m	Grid 9 M4 0.055 A/m

Cursor:
Total = 0.1017 A/m
H Category: M4
Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band IV-1513CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

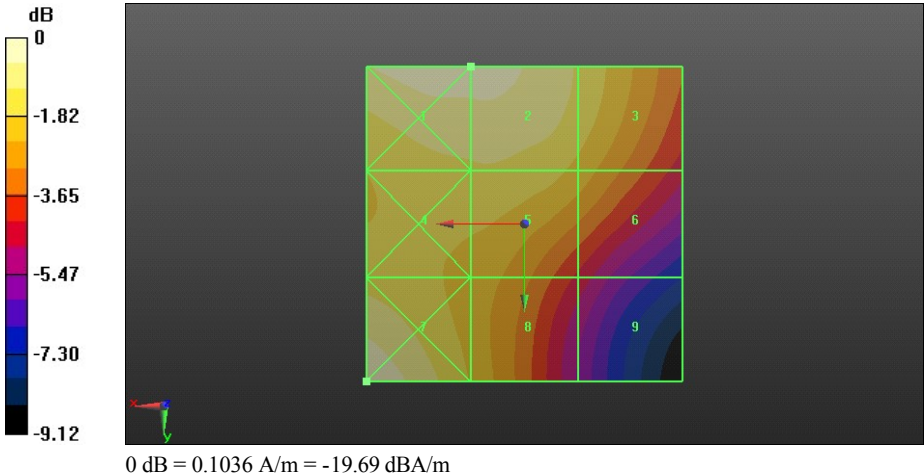
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09200 A/m; Power Drift = -0.13 dB
PMF = 0.9800 is applied.
H-field emissions = 0.09970 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.100 A/m	Grid 2 M4 0.100 A/m	Grid 3 M4 0.089 A/m
Grid 4 M4 0.089 A/m	Grid 5 M4 0.089 A/m	Grid 6 M4 0.082 A/m
Grid 7 M4 0.104 A/m	Grid 8 M4 0.084 A/m	Grid 9 M4 0.062 A/m

Cursor:
Total = 0.1036 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band V-4233CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

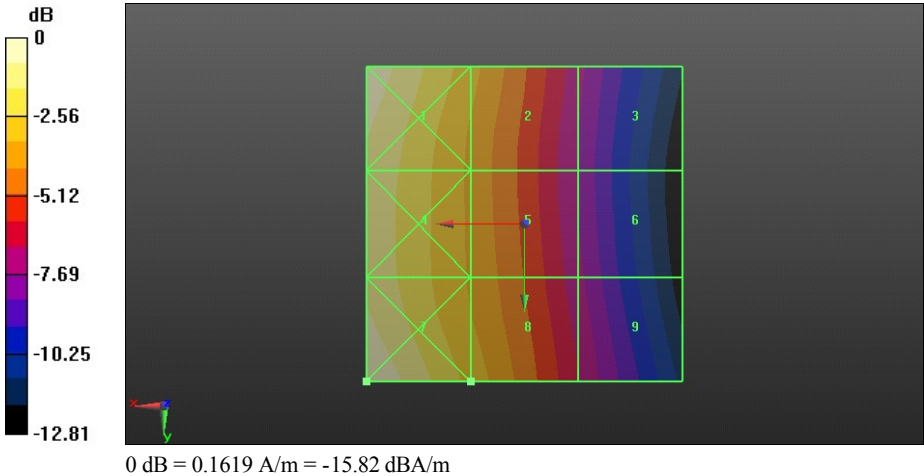
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from
Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09000 A/m; Power Drift = -0.00 dB
PMF = 1.020 is applied.
H-field emissions = 0.1168 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.158 A/m	Grid 2 M4 0.114 A/m	Grid 3 M4 0.069 A/m
Grid 4 M4 0.144 A/m	Grid 5 M4 0.108 A/m	Grid 6 M4 0.069 A/m
Grid 7 M4 0.162 A/m	Grid 8 M4 0.117 A/m	Grid 9 M4 0.074 A/m

Cursor:
Total = 0.1619 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band V-4182CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

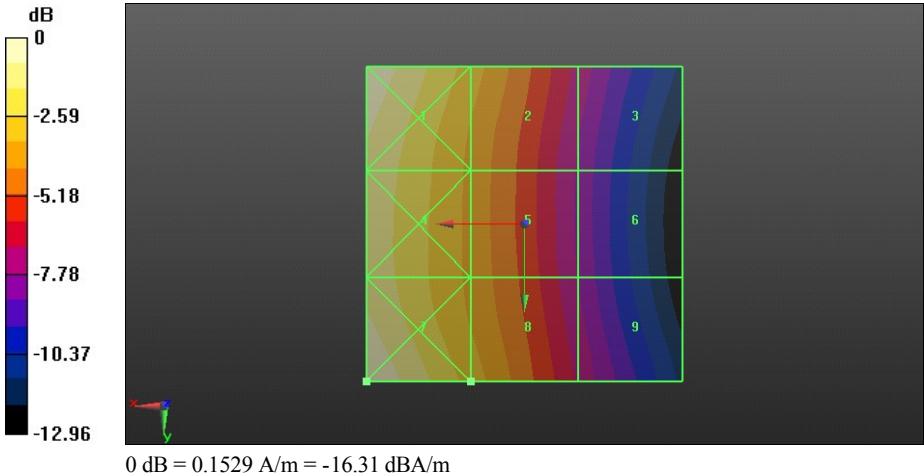
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08400 A/m; Power Drift = -0.03 dB
PMF = 1.020 is applied.
H-field emissions = 0.1090 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.151 A/m	Grid 2 M4 0.108 A/m	Grid 3 M4 0.067 A/m
Grid 4 M4 0.136 A/m	Grid 5 M4 0.100 A/m	Grid 6 M4 0.062 A/m
Grid 7 M4 0.153 A/m	Grid 8 M4 0.109 A/m	Grid 9 M4 0.068 A/m

Cursor:
Total = 0.1529 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band V-4132CH

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

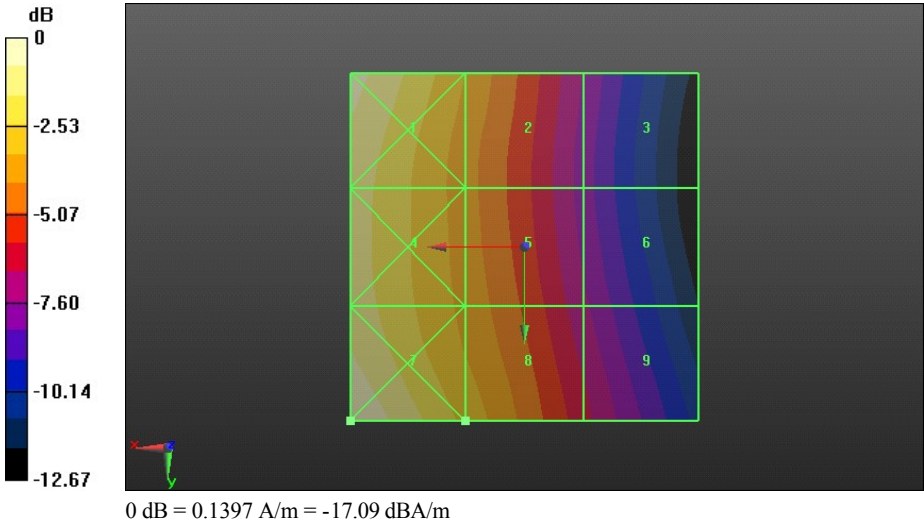
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07700 A/m; Power Drift = -0.05 dB
PMF = 1.020 is applied.
H-field emissions = 0.1018 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.133 A/m	Grid 2 M4 0.095 A/m	Grid 3 M4 0.058 A/m
Grid 4 M4 0.122 A/m	Grid 5 M4 0.092 A/m	Grid 6 M4 0.060 A/m
Grid 7 M4 0.140 A/m	Grid 8 M4 0.102 A/m	Grid 9 M4 0.067 A/m

Cursor:
Total = 0.1397 A/m
H Category: M4
Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_Y301-A2-UMTS Band V-4233CH with battery 2#

DUT: Y301-A2; Type: LTE/UMTS Smart Phone; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$
Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09100 A/m; Power Drift = 0.01 dB
PMF = 1.020 is applied.
H-field emissions = 0.1167 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.160 A/m	Grid 2 M4 0.117 A/m	Grid 3 M4 0.072 A/m
Grid 4 M4 0.146 A/m	Grid 5 M4 0.109 A/m	Grid 6 M4 0.069 A/m
Grid 7 M4 0.162 A/m	Grid 8 M4 0.116 A/m	Grid 9 M4 0.073 A/m

Cursor:
Total = 0.1618 A/m
H Category: M4
Location: 25, 25, 8.7 mm

